

MCR100 Series

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

Features

- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 V
- On-State Current Rating of 0.8 A RMS at 80°C
- High Surge Current Capability – 10 A
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dV/dt – 20 V/ μ sec Minimum at 110°C
- Glass-Passivated Surface for Reliability and Uniformity
- Pb-Free Packages are Available*



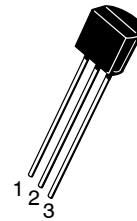
ON Semiconductor®

<http://onsemi.com>

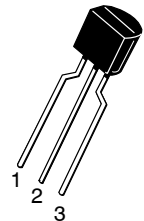
SCRs
0.8 A RMS
100 thru 600 V



**TO-92
CASE 29
STYLE 10**

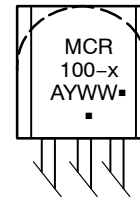


**STRAIGHT LEAD
BULK PACK**



**BENT LEAD
TAPE & REEL
AMMO PACK**

MARKING DIAGRAM



- x = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

PIN ASSIGNMENT	
1	Cathode
2	Gate
3	Anode

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MCR100 Series

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Notes 1 and 2) (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz; R _{GK} = 1 kΩ)	V _{DRM} , V _{RRM}	MCR100-3 MCR100-4 MCR100-6 MCR100-8	V
On-State RMS Current, (T _C = 80°C) 180° Conduction Angles	I _{T(RMS)}	0.8	A
Peak Non-Repetitive Surge Current, (1/2 Cycle, Sine Wave, 60 Hz, T _J = 25°C)	I _{TSM}	10	A
Circuit Fusing Consideration, (t = 8.3 ms)	I ² t	0.415	A ² s
Forward Peak Gate Power, (T _A = 25°C, Pulse Width ≤ 1.0 μs)	P _{GM}	0.1	W
Forward Average Gate Power, (T _A = 25°C, t = 8.3 ms)	P _{G(AV)}	0.01	W
Forward Peak Gate Current, (T _A = 25°C, Pulse Width ≤ 1.0 μs)	I _{GM}	1.0	A
Reverse Peak Gate Voltage, (T _A = 25°C, Pulse Width ≤ 1.0 μs)	V _{G(RM)}	5.0	V
Operating Junction Temperature Range @ Rate V _{RRM} and V _{DRM}	T _J	-40 to 110	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- See ordering information for exact device number options.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	R _{θJC} R _{θJA}	75 200	°C/W
Lead Solder Temperature (< 1/16" from case, 10 secs max)	T _L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current (Note 3) (V _D = Rated V _{DRM} and V _{RRM} ; R _{GK} = 1 kΩ)	I _{DRM} , I _{RRM}	-	-	10	μA
		-	-	100	

ON CHARACTERISTICS

Peak Forward On-State Voltage* (I _{TM} = 1.0 A Peak @ T _A = 25°C)	V _{TM}	-	-	1.7	V
Gate Trigger Current (Note 4) T _C = 25°C (V _{AK} = 7.0 Vdc, R _L = 100 Ω)	I _{GT}	-	40	200	μA
Holding Current (Note 3) T _C = 25°C (V _{AK} = 7.0 Vdc, Initiating Current = 20 mA, R _{GK} = 1 kΩ) T _C = -40°C	I _H	-	0.5	5.0	mA
		-	-	10	
Latch Current (Note 4) T _C = 25°C (V _{AK} = 7.0 V, I _g = 200 μA) T _C = -40°C	I _L	-	0.6	10	mA
		-	-	15	
Gate Trigger Voltage (Note 4) T _C = 25°C (V _{AK} = 7.0 Vdc, R _L = 100 Ω) T _C = -40°C	V _{GT}	-	0.62	0.8	V
		-	-	1.2	

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, R _{GK} = 1 kΩ, T _J = 110°C)	dV/dt	20	35	-	V/μs
Critical Rate of Rise of On-State Current (I _{PK} = 20 A; P _w = 10 μsec; diG/dt = 1 A/μsec, I _{gt} = 20 mA)	di/dt	-	-	50	A/μs

*Indicates Pulse Test: Pulse Width ≤ 1.0 ms, Duty Cycle ≤ 1%.

3. R_{GK} = 1000 Ω included in measurement.

4. Does not include R_{GK} in measurement.